

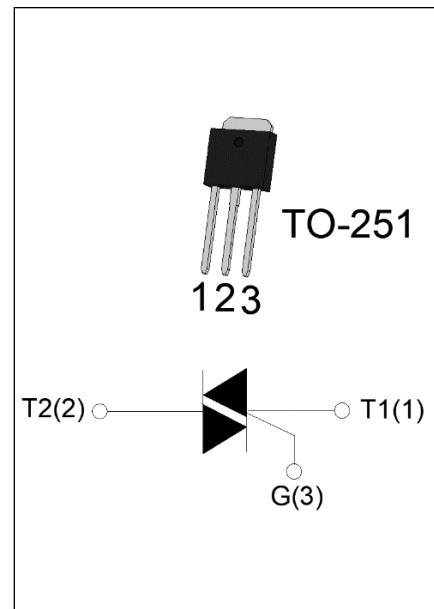


## JST137H-800DX 8A TRIAC

Rev.A.1.0

**DESCRIPTION:**

The JST137H-800DX triac is suitable for general purpose AC switching. It can be used as an ON/OFF function in applications such as heating regulation, induction motor starting circuits, for phase control operation in light dimmers, motor speed controllers. From T2 terminals to external heatsink. Package TO-251 is RoHS compliant.

**MAIN FEATURES**

Symbol	Value	Unit
$I_{T(\text{RMS})}$	8	A
$V_{\text{DRM}} / V_{\text{RRM}}$	800	V
$I_{G(\text{T I/II/III/IV})}$	5/5/5/10	mA

**ABSOLUTE MAXIMUM RATINGS**

Parameter	Symbol	Value	Unit
Storage junction temperature range	$T_{\text{stg}}$	-40-150	°C
Operating junction temperature range	$T_j$	-40-125	°C
Repetitive peak off-state voltage ( $T_j=25^\circ\text{C}$ )	$V_{\text{DRM}}$	800	V
Repetitive peak reverse voltage ( $T_j=25^\circ\text{C}$ )	$V_{\text{RRM}}$	800	V
RMS on-state current ( $T_c \leqslant 65^\circ\text{C}$ )	$I_{T(\text{RMS})}$	8	A
Non repetitive surge peak on-state current (full cycle , $t_p=20\text{ms}$ , $T_j=25^\circ\text{C}$ )	$I_{\text{TSM}}$	55	A
Non repetitive surge peak on-state current (full cycle , $t_p=16.6\text{ms}$ , $T_j=25^\circ\text{C}$ )		61	
$I^2t$ value for fusing ( $t_p=10\text{ms}$ , $T_j=25^\circ\text{C}$ )	$I^2t$	15.125	$\text{A}^2\text{s}$
Critical rate of rise of on-state current ( $I_G=2 \times I_{GT}$ , $f=100\text{Hz}$ , $T_j=125^\circ\text{C}$ )	I - II - III IV	50	$\text{A}/\mu\text{s}$
		30	
Peak gate current ( $t_p=20\mu\text{s}$ , $T_j=125^\circ\text{C}$ )	$I_{GM}$	2	A
Average gate power dissipation ( $T_j=125^\circ\text{C}$ )	$P_{G(\text{AV})}$	0.5	W
Peak gate power	$P_{GM}$	5	W
Peak pulse voltage ( $T_j=25^\circ\text{C}$ ; non-repetitive,off-state;FIG.7)	$V_{pp}$	3.5	kV

ELECTRICAL CHARACTERISTICS ( $T_j=25^\circ\text{C}$  unless otherwise specified)

Symbol	Test Condition	Quadrant	Value		Unit
$I_{GT}$	$V_D=12\text{V}$ $R_L=33\Omega$	I - II - III	MAX.	5	mA
		IV		10	
$V_{GT}$	ALL		MAX.	1	V
$V_{GD}$	$V_D=V_{DRM}$ $T_j=125^\circ\text{C}$ $R_L=3.3\text{K}\Omega$	ALL	MIN.	0.2	V
$I_L$	$I_G=1.2I_{GT}$	I - III - IV	MAX.	20	mA
		II		30	
$I_H$	$I_T=100\text{mA}$		MAX.	15	mA
$dV/dt$	$V_D=540\text{V}$ Gate Open $T_j=125^\circ\text{C}$		MIN.	80	V/ $\mu\text{s}$
$(dV/dt)c$	$(dI/dt)c=2\text{A/ms}$ , $T_j=125^\circ\text{C}$		MIN.	2	V/ $\mu\text{s}$
$t_{on}$	$I_G=20\text{mA}$ $I_A=200\text{mA}$ $I_R=20\text{mA}$ $T_j=25^\circ\text{C}$	TYP.	1.5	$\mu\text{s}$	
			15		

## STATIC CHARACTERISTICS

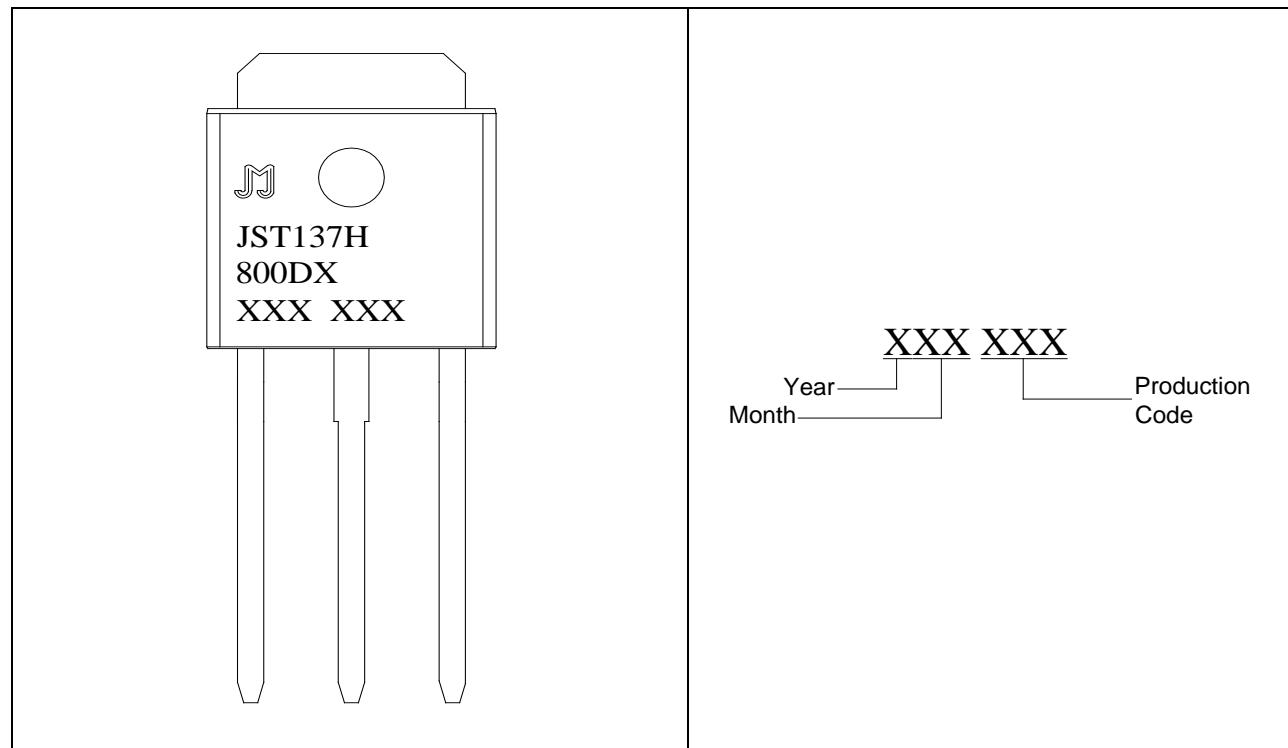
Symbol	Parameter		Value(MAX.)	Unit
$V_{TM}$	$I_{TM}=10\text{A}$	$t_p=380\mu\text{s}$	$T_j=25^\circ\text{C}$	1.6 V
$V_{TO}$	Threshold voltage		$T_j=125^\circ\text{C}$	0.86 V
$R_D$	Dynamic resistance		$T_j=125^\circ\text{C}$	75 m $\Omega$
$I_{DRM}$	$V_D=V_{DRM}$ $V_R=V_{RRM}$		$T_j=25^\circ\text{C}$	5 $\mu\text{A}$
			$T_j=125^\circ\text{C}$	0.45 mA

## THERMAL RESISTANCES

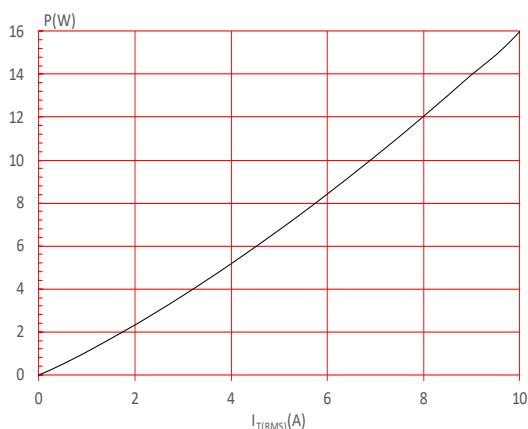
Symbol	Parameter	Value	Unit
$R_{th(j-c)}$	junction to case (AC)	5	°C/W
$R_{th(j-a)}$	junction to ambient (AC)	120	°C/W

**ORDERING INFORMATION**

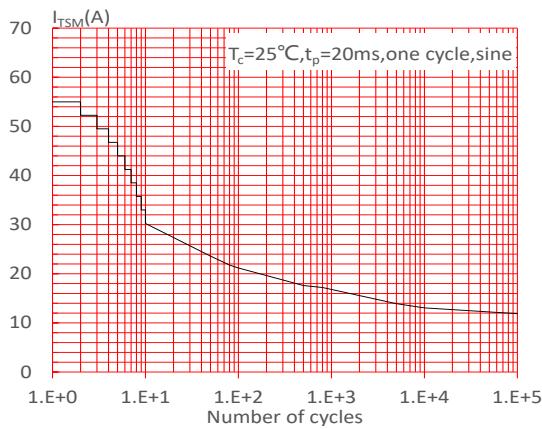
<b>J</b>	<b>ST</b>	<b>137</b>	<b>H</b>	<b>-800</b>	<b>D</b>	<b>X</b>
JieJie Microelectronics Co., Ltd.						
	Triacs					X:Small current
		I <sub>T</sub> (RMS):8A				D:I <sub>GT1-3</sub> ≤5mA I <sub>GT4</sub> ≤10mA
			H:TO-251			
				800:V <sub>DRM</sub> /V <sub>RRM</sub> ≥800V		

**MARKING**

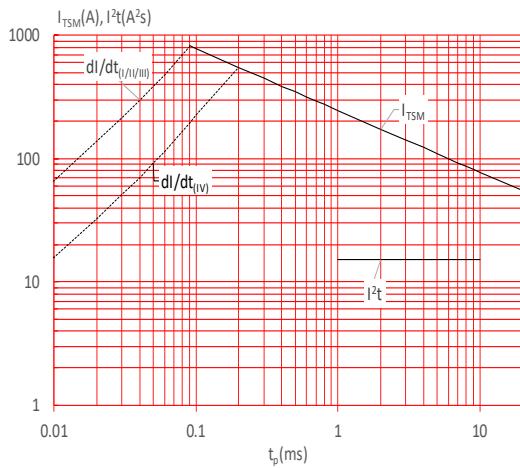
**FIG.1** Maximum power dissipation versus RMS on-state current



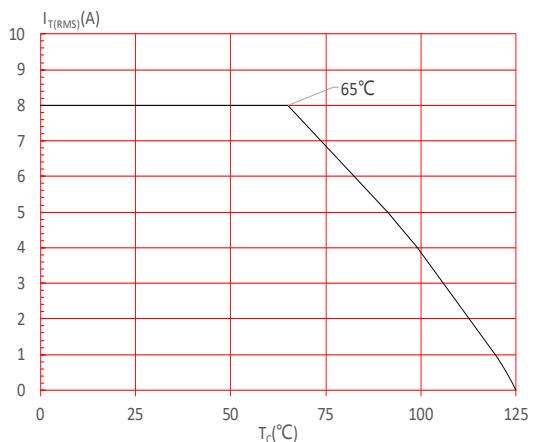
**FIG.3:** Surge peak on-state current versus number of cycles



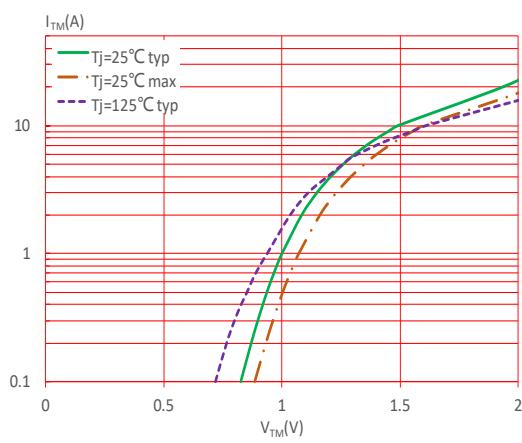
**FIG.5:** Non-repetitive surge peak on-state current for a sinusoidal pulse with width  $t_p < 20\text{ms}$ , and corresponding value of  $I^2t$  ( I - II - III:  $\text{d}I/\text{d}t < 50\text{A}/\mu\text{s}$ ; IV:  $\text{d}I/\text{d}t < 30\text{A}/\mu\text{s}$ )



**FIG.2:** RMS on-state current versus case temperature



**FIG.4:** On-state characteristics



**FIG.6:** Relative variations of gate trigger current, holding current and latching current versus junction temperature

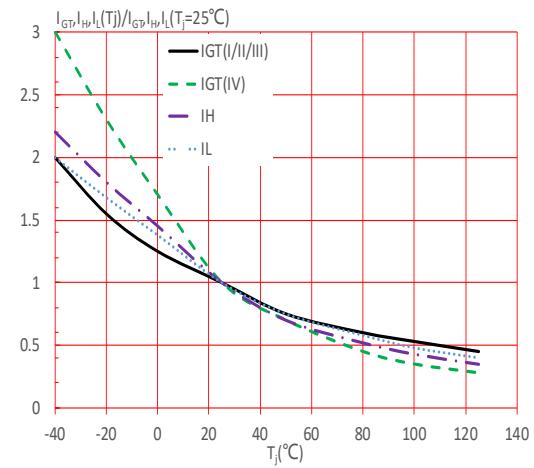
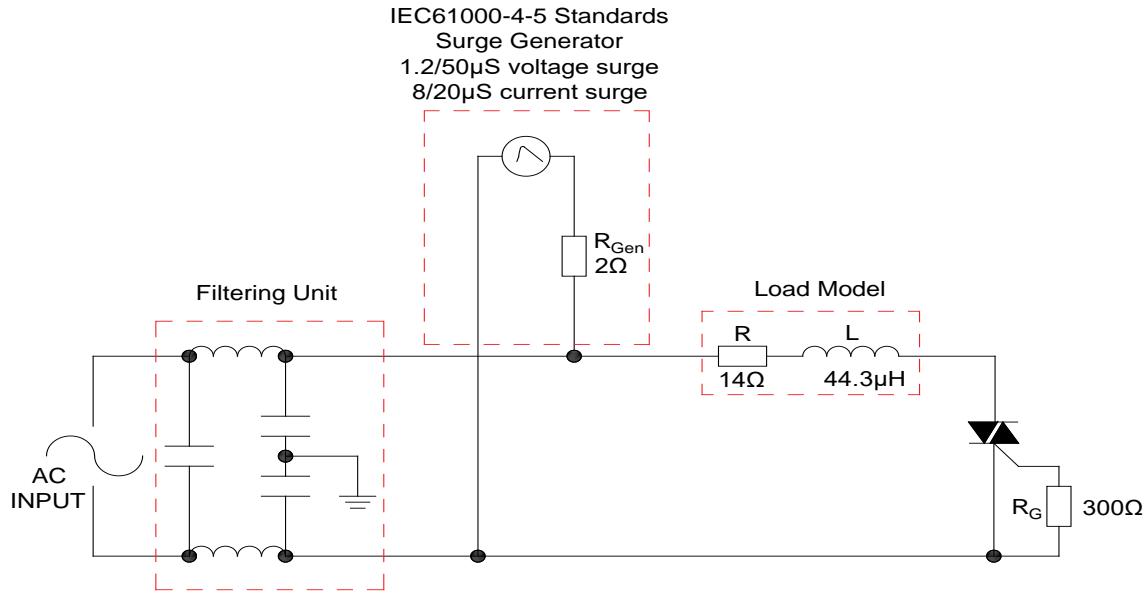


FIG.7: Test circuit for inductive and resistive loads to IEC-61000-4-5 standards



## SHAPING AND SOLDERING PARAMETERS

Refer to 《Instructions for installation of plastic-sealed in-line power devices》 released by JieJie.

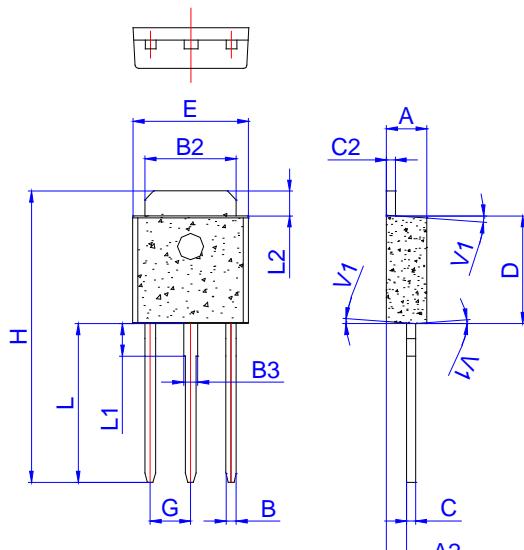
**ORDERING INFORMATION**

Order code	Voltage $V_{DRM}/V_{RRM}$ (V)	IGT(mA)		Package	Base qty. (pcs)	Delivery mode
		I - II - III	IV			
<b>JST137H-800DX</b>	<b>800</b>	<b>5</b>	<b>10</b>	<b>TO-251</b>	<b>80</b>	<b>Tube</b>

**Document Revision History**

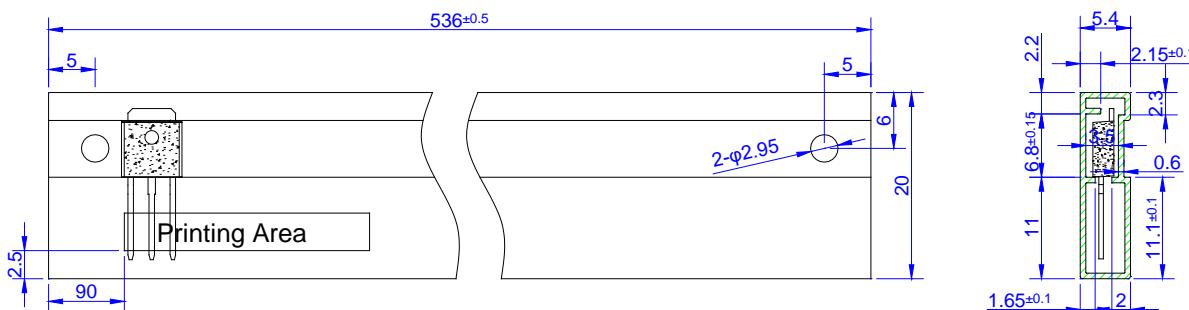
Date	Revision	Changes
Apr.14, 2023	A.1.0	Last updated

## PACKAGE MECHANICAL DATA



Ref.	Dimensions					
	Millimeters			Inches		
	Min.	Typ.	Max.	Min.	Typ.	Max.
A	2.20		2.40	0.086		0.095
A2	1.00		1.30	0.039		0.051
B	0.50		0.70	0.020		0.028
B2	5.10		5.40	0.200		0.213
B3	0.70		1.00	0.028		0.039
C	0.45		0.62	0.018		0.024
C2	0.48		0.62	0.019		0.024
D	6.00		6.20	0.236		0.244
E	6.40		6.70	0.252		0.264
G	2.20		2.40	0.087		0.094
H	16.0		17.0	0.630		0.669
L	8.90		9.40	0.350		0.370
L1	1.80		2.20	0.071		0.087
L2	1.25		1.55	0.049		0.061
V1			4°			4°

## DELIVERY MODE



PACKAGE	OUTLINE	TUBE (PCS)	INNER BOX (PCS)	PER CARTON
TO-251	TUBE	80	4,000	20,000

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